

ABSTRACT

Provided is a polishing composition containing abrasive grains, at least one type of alcohol compound selected from the group consisting of aliphatic alcohols with 2 to 6 carbon atoms and glycol ethers with 3 to 10 carbon atoms, at least one type of basic compound selected from the group consisting of quaternary ammonium salts and alkali metal salts, and water. The average primary particle diameter of the abrasive grains is 5 to 50 nm. The content of the alcohol compound in the polishing composition is 0.01 to 1% by mass. The polishing composition is mainly used in an application of polishing a semiconductor substrate surface.